

# Piezo Haptic Driver with Integrated Boost Converter

Check for Samples: DRV8662

## **FEATURES**

- High-Voltage Piezo Haptic Driver
  - Drives up to 100 nF at 200 V<sub>PP</sub> and 300 Hz
  - Drives up to 150 nF at 150 V<sub>PP</sub> and 300 Hz
  - Drives up to 330 nF at 100 V<sub>PP</sub> and 300 Hz
  - Drives up to 680 nF at 50 V<sub>PP</sub> and 300 Hz
  - Differential Output
- Integrated Boost Converter
  - Adjustable Boost Voltage
  - Adjustable Current Limit
  - Integrated Power FET and Diode
  - No Transformer Required
- Fast Start Up Time of 1.5 ms
- Wide Supply Voltage Range of 3.0 V to 5.5 V
- 1.8V Compatible Digital Pins
- Thermal Protection
- Available in a 4 mm x 4 mm x 0.9 mm QFN package (RGP)

#### **APPLICATIONS**

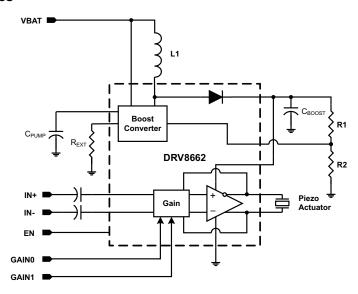
- Mobile Phones
- Tablets
- Portable Computers
- Keyboards and Mice
- Touch Enabled Devices

## **DESCRIPTION**

The DRV8662 is a single-chip piezo haptic driver with integrated 105 V boost switch, integrated power diode, and integrated fully-differential amplifier. This versatile device is capable of driving both high-voltage and low-voltage piezo haptic actuators. The input signal can be either differential or single-ended. The DRV8662 supports four GPIO-controlled gains: 28.8 dB, 34.8 dB, 38.4 dB, and 40.7 dB.

The boost voltage is set using two external resistors, and the boost current limit is programmable via the  $R_{\text{EXT}}$  resistor. The boost converter architecture will not allow the demand on the supply current to exceed the limit set by the  $R_{\text{EXT}}$  resistor; therefore, the DRV8662 is well-suited for portable applications. This feature also allows the user to optimize the DRV8662 circuit for a given inductor based on the desired performance requirements.

A typical start-up time of 1.5 ms makes the DRV8662 an ideal piezo driver for fast haptic responses. Thermal overload protection prevents the device from being damaged when overdriven.





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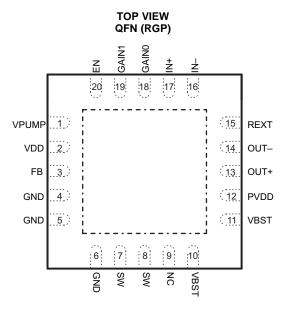


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ORDERING INFORMATION**

	QFN (RGP) 4mm x 4 mm x 0.9 mm
Device	DRV8662RGPR
Symbolization	8662

## PINOUT INFORMATION



## **PIN FUNCTIONS**

	PIN	INPUT/ OUTPUT/	DECORIDATION			
NAME	NO. (RGP)	POWER (I/O/P)	DESCRIPTION			
IN+	17	I	Non-inverting input			
IN-	16	1	Inverting input			
OUT+	13	0	Non-inverting output			
OUT-	14	0	Inverting output			
VDD	2	Р	Power supply (connect to battery)			
GND	4, 5, 6	Р	Ground			
SW	7, 8	Р	Internal boost switch pin			
PVDD	12	Р	Amplifier supply voltage			
GAIN0	18	I	Gain programming pin – LSB			
GAIN1	19	I	Gain programming pin – MSB			
EN	20	I	Chip enable			
VPUMP	1	Р	Internal Charge-pump voltage			
FB	3	I	Boost feedback			
VBST	10, 11	Р	Boost output voltage			
REXT	15	I	Resistor to ground, sets boost current limit			



# **ABSOLUTE MAXIMUM RATINGS**(1)

Over operating free-air temperature range (unless otherwise noted)

			VALUE	UNIT		
	Supply voltage	VDD	-0.3 to 6.0	V		
$V_{I}$	Input voltage	IN+, IN-, EN, GAIN0, GAIN1, FB	$-0.3$ to $V_{DD} + 0.3$	V		
	Boost/Output Voltage	Output Voltage PVDD, SW, OUT+, OUT-				
$T_A$	Operating free-air temperatu	-40 to 70	°C			
$T_J$	Operating junction temperatu	ire range	-40 to 150	°C		
T <sub>stg</sub>	Storage temperature range		-65 to 85	°C		
	Lead temperature 1.6 mm (1	/16 inch) from case for 10 seconds (RGP)	260	°C		
	ESD Protection	НВМ	2500	V		
	ESD FIDIBUIUM	CDM	1500	V		

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operations of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## RECOMMENDED OPERATING CONDITIONS

				MIN	TYP	MAX	UNIT
$V_{DD}$	Supply voltage	VDD		3.0		5.5	V
$V_{BST}$	Boost voltage	VBST		15		105	V
V <sub>IN</sub>	Differential input vol	tage			1.8 <sup>(1)</sup>		V
		VBST = 105 V, Frequency = 500	Hz, V <sub>O,PP</sub> = 200 V			50	
		VBST = 105 V, Frequency = 300			100		
		VBST = 80 V, Frequency = 300 H			150	nF	
$C_L$	Load capacitance	VBST = 55 V, Frequency = 300 H			330		
		VBST = 30 V, Frequency = 300 I			680		
		VBST = 25 V, Frequency = 300 H			1		
		VBST = 15 V, Frequency = 300 H			3	μF	
V <sub>IL</sub>	Digital input low voltage	EN, GAIN0, GAIN1	V <sub>DD</sub> = 3.6 V			0.75	V
V <sub>IH</sub>	Digital input high voltage	EN, GAIN0, GAIN1	V <sub>DD</sub> = 3.6 V	1.4			V
R <sub>EXT</sub>	Current limit control	limit control resistor					kΩ
L	Inductance for Boos	3.3			μH		

<sup>(1)</sup> Gains are optimized for a 1.8V peak input

### THERMAL INFORMATION

	THERMAL METRIC <sup>(1)</sup>	DRV8662	LINUTO	
	THERMAL METRIC	RGP (20 PINS)	UNITS	
$\theta_{JA}$	Junction-to-ambient thermal resistance	33.1		
$\theta_{JCtop}$	Junction-to-case (top) thermal resistance	30.9		
$\theta_{JB}$	Junction-to-board thermal resistance	8.7	9 <b>C</b> /M	
Ψлт	Junction-to-top characterization parameter	0.4	°C/W	
ΨЈВ	Junction-to-board characterization parameter	8.7		
$\theta_{JCbot}$	Junction-to-case (bottom) thermal resistance	2.5		

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



# **ELECTRICAL CHARACTERISTICS**

 $\underline{T_{\text{A}}} = 25^{\circ}\text{C}, \ V_{\text{O,PP}} = V_{\text{OUT+}} - V_{\text{OUT-}} = 200 \ \text{V}, \ C_{\text{L}} = 47 \ \text{nF}, \ A_{\text{V}} = 40 \ \text{dB}, \ L = 4.7 \ \mu\text{H} \ \text{(unless otherwise noted)}$ 

	PARAMETER	TEST CON	TEST CONDITIONS				
I <sub>IL</sub>	Digital input low current	EN, GAIN0, GAIN1	$V_{DD} = 3.6 \text{ V}, V_{IN} = 0 \text{ V}$		1	μA	
I <sub>IH</sub>	Digital input high current	EN, GAIN0, GAIN1	$V_{DD} = 3.6 \text{ V}, V_{IN} = V_{DD}$		5	μA	
$I_{SD}$	Shut down current	$V_{DD} = 3.6 \text{ V}, V_{EN} = 0 \text{ V}$		13	1	μA	
		$V_{DD} = 3.6 \text{ V}, V_{EN} = V_{DD}, VBST$	= 105 V, no signal	24		mA	
	Quiescent current	$V_{DD} = 3.6 \text{ V}, V_{EN} = V_{DD}, VBST$	= 80 V, no signal	13	1	mA	
I <sub>DDQ</sub>	Quiescent current	$V_{DD} = 3.6 \text{ V}, V_{EN} = V_{DD}, VBST$	= 55 V, no signal	9	1	mA	
		$V_{DD} = 3.6 \text{ V}, V_{EN} = V_{DD}, VBST$	= 30 V, no signal	5	;	mA	
R <sub>IN</sub>	Input impedance	All gains		100	1	kΩ	
		GAIN<1:0> = 00		28.8	1		
^	Amplifier gain	GAIN<1:0> = 01	34.8	}	dB		
$A_V$		GAIN<1:0> = 10	38.4	ļ			
		GAIN<1:0> = 11	40.7	•			
	A constition Donadovidab	GAIN<1:0> = 00, $V_{O,PP}$ = 50 V,	20	1			
BW		GAIN<1:0> = 01, $V_{O,PP}$ = 100 $V_{O,PP}$	10	)	kHz		
DVV	Amplifier Bandwidth	GAIN<1:0> = 10, $V_{O,PP}$ = 150 $V_{O,PP}$	7.5	i	KΠZ		
		GAIN<1:0> = 11, V <sub>O,PP</sub> = 200 V	5	i			
		$V_{DD} = 3.6 \text{ V}, C_L = 10 \text{ nF}, f = 150 \text{ nF}$	0 Hz, V <sub>O,PP</sub> = 200 V	75	;		
	Average battery current	$V_{DD} = 3.6 \text{ V}, C_L = 10 \text{ nF}, f = 30$	0 Hz, V <sub>O,PP</sub> = 200 V	115	;	m Λ	
I <sub>BAT, AVG</sub>	during operation	$V_{DD} = 3.6 \text{ V}, C_L = 47 \text{ nF}, f = 150 \text{ m}$	0 Hz, V <sub>O,PP</sub> = 200 V	210	)	mA	
		$V_{DD} = 3.6 \text{ V}, C_L = 47 \text{ nF}, f = 30$	400	)			
THD+N	Total harmonic distortion plus noise	f = 300 Hz, V <sub>O,PP</sub> = 200 V		1		%	
t <sub>SU</sub>	Start-up time	V <sub>DD</sub> = 3.6 V, time from EN high fully enabled	until boost and amplifier are	1.5	i	ms	

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#### TYPICAL CHARACTERISTICS

 $V_{DD} = 3.6~V,~R_{EXT} = 7.5~k\Omega,~L = 4.7~\mu H,~Differential~Input$ 

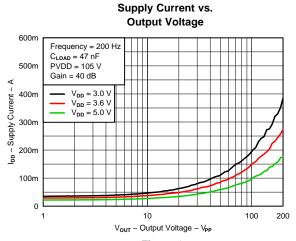


Figure 1.

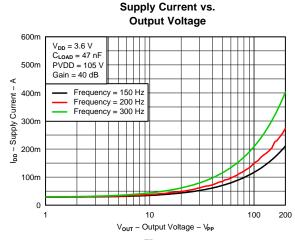


Figure 2.

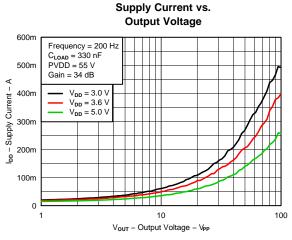
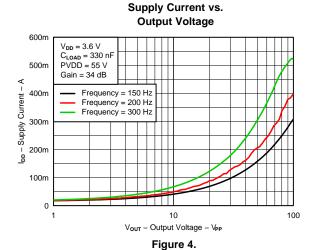
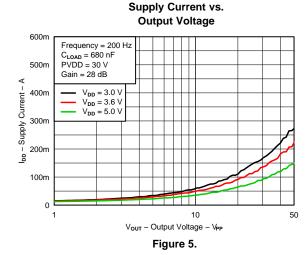
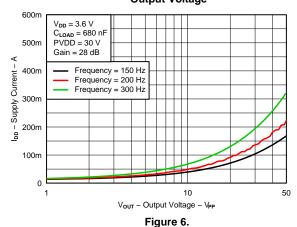


Figure 3.



Supply Current vs.
Output Voltage





•



## TYPICAL CHARACTERISTICS (continued)

 $V_{DD} = 3.6$  V,  $R_{EXT} = 7.5$  kΩ,  $L = 4.7~\mu H,$  Differential Input

# Total Harmonic Distortion + Noise vs.

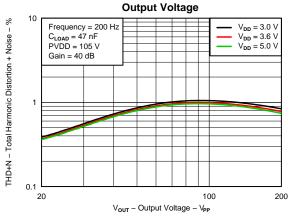


Figure 7.

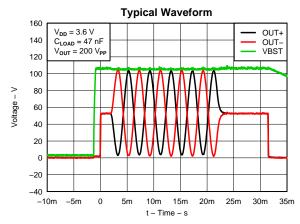


Figure 8.

#### Total Harmonic Distortion + Noise vs. **Output Voltage**

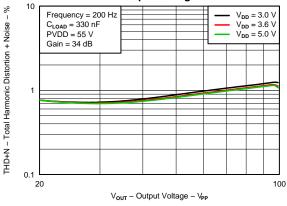


Figure 9.

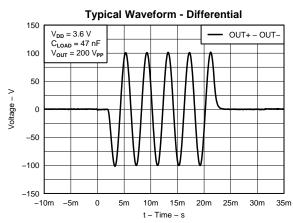


Figure 10.

# Total Harmonic Distortion + Noise vs.

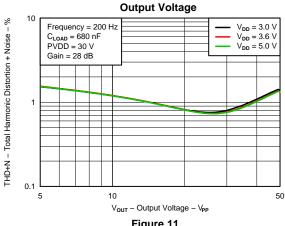


Figure 11.

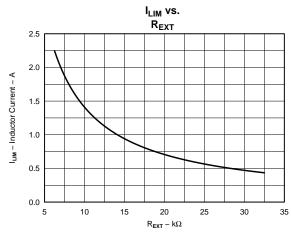


Figure 12.

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#### DETAILED DESCRIPTION

#### **OPERATION**

The DRV8662 accepts the typical battery range used in portable applications (3.0 V to 5.5 V) and creates a boosted supply rail with an integrated DC-DC converter. This boosted supply rail is fed to an internal, high-voltage, fully-differential amplifier that is capable of driving capacitive loads such as piezos with signals up to 200  $V_{PP}$ . No transformer is required for boost operation. Only a single inductor is needed. The boost power FET and power diode are both integrated within the device.

## **FAST START-UP (ENABLE PIN)**

The DRV8662 features a fast startup time, which is essential for achieving low latency in haptic applications. When the EN pin transitions from low to high, the boost supply is turned on, the input capacitor is pre-charged, and the amplifier is enabled in a typical 1.5 ms total startup time. In the system application, the entire system latency should be kept to less than 30 ms total to be imperceptible to the end user. At 1.5 ms, the DRV8662 will be a small percentage of the total system latency.

#### **GAIN CONTROL**

The gain from IN+/IN- to OUT+/OUT- is given by the table below.

GAIN1	GAIN0	Gain (dB)
0	0	28.8
0	1	34.8
1	0	38.4
1	1	40.7

The gains are optimized to achieve approximately 50  $V_{PP}$ , 100  $V_{PP}$ , 150  $V_{PP}$ , or 200  $V_{PP}$  at the output without clipping from a 1.8 V peak single-ended input signal source.

#### ADJUSTABLE BOOST VOLTAGE

The output voltage of the integrated boost converter may be adjusted by a resistive feedback divider between the boost output voltage (VBST) and the feedback pin (FB). The boost voltage should be programmed to a value greater than the maximum peak signal voltage that the user expects to create with the DRV8662 amplifier. Lower boost voltages will achieve better system efficiency when lower amplitude signals are applied, so the user should take care not to use a higher boost voltage than necessary. The maximum allowed boost voltage is 105V.

### ADJUSTABLE BOOST CURRENT LIMIT

The current limit of the boost switch may be adjusted via a resistor to ground placed on the REXT pin. The programmed current limit should be less than the rated saturation limit of the inductor selected by the user to avoid damage to both the inductor and the DRV8662. If the combination of the programmed limit and inductor saturation is not high enough, then the output current of the boost converter will not be high enough to regulate the boost output voltage under heavy load conditions. This will, in turn, cause the boosted rail to sag, possibly causing distortion of the output waveform.

#### INTERNAL CHARGE PUMP

The DRV8662 has an integrated charge pump to provide adequate gate drive for internal nodes. The output of this charge pump is placed on the VPUMP pin. An X5R or X7R storage capacitor of 0.1  $\mu$ F with a voltage rating of 10 V or greater must be placed at this pin.



### THERMAL SHUTDOWN

The DRV8662 contains an internal temperature sensor that will shut down both the boost converter and the amplifier when the temperature threshold is exceeded. When the die temperature falls below the threshold, the device will restart operation automatically as long as the EN pin is high. Continuous operation of the DRV8662 is not recommended. Most haptic use models only operate the DRV8662 in short bursts. The thermal shutdown function will protect the DRV8662 from damage when overdriven, but usage models which drive the DRV8662 into thermal shutdown should always be avoided.

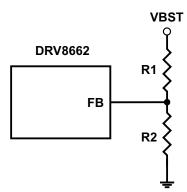
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#### APPLICATION INFORMATION

### PROGRAMMING THE BOOST VOLTAGE

The boost output voltage (VBST) is programmed via two external resistors as shown in the diagram below.



The boost output voltage is given by Equation 1

$$V_{BOOST} = V_{FB} \left( 1 + \frac{R_1}{R_2} \right) \tag{1}$$

where  $V_{FB} = 1.32 \text{ V}$ .

VBST should be programmed to a value 5.0 V greater than the largest peak voltage expected in the system to allow adequate amplifier headroom. Since the programming range for the boost voltage extends to 105 V, the leakage current through the resistor divider can become significant. It is recommended that the sum of the resistance of R1 and R2 be greater than 500 k $\Omega$ . Note that when resistor values greater than 1 M $\Omega$  are used, PCB contamination may cause boost voltage inaccuracy. Exercise caution when soldering large resistances, and clean the area when finished for best results.

#### PROGRAMING THE BOOST CURRENT LIMIT

The peak current drawn from the supply through the inductor is set solely by the  $R_{EXT}$  resistor. Note that this peak current limit is independent of the inductance value chosen, but the inductor should be capable of handling this programmed limit. The relationship of  $R_{EXT}$  to  $I_{LIM}$  is approximated by Equation 2.

$$R_{EXT} = \left(K \frac{V_{REF}}{I_{LIM}}\right) - R_{INT}$$
 (2)

where K = 10500,  $V_{REF}$  = 1.35 V,  $R_{INT}$  = 60  $\Omega$ , and  $I_{LIM}$  is the desired peak current limit through the inductor.

#### INDUCTOR SELECTION

Inductor selection plays a critical role in the performance of the DRV8662. The range of recommended inductances is from 3.3  $\mu$ H to 22  $\mu$ H. In general, higher inductances within a given manufacturer's inductor series have lower saturation current limits, and vice-versa. When a larger inductance is chosen, the DRV8662 boost converter will automatically run at a lower switching frequency and incur less switching losses; however, larger values of inductance may have higher equivalent series resistance (ESR), which will increase the parasitic inductor losses. Since lower values of inductance generally have higher saturation currents, they are a better choice when attempting to maximize the output current of the boost converter. The following table has sample inductors that provide adequate performance.

For inductor recommendations, see DRV8662EVM User's Guide (SLOU302)



#### PIEZO ACTUATOR SELECTION

There are several key specifications to consider when choosing a piezo actuator for haptics such as dimensions, blocking force, and displacement. However, the key electrical specifications from the driver perspective are voltage rating and capacitance. At the maximum frequency of 500 Hz, the DRV8662 is optimized to drive up to  $50 \, \text{nF}$  at  $200 \, \text{V}_{PP}$ , which is the highest voltage swing capability. It will drive larger capacitances if the programmed boost voltage is lowered and/or the user limits the input frequency range to lower frequencies (e.g.  $300 \, \text{Hz}$ ).

For piezo actuator recommendations, see the DRV8662EVM User's Guide (SLOU302).

#### **BOOST CAPACITOR SELECTION**

The boost output voltage may be programmed as high as 105V. A capacitor with a voltage rating of at least the boost output voltage must be selected. Since ceramic capacitors tend to come in ratings of 100 V or 250 V, a 250 V rated 100 nF capacitor of the X5R or X7R type is recommended for the 105 V case. The selected capacitor should have a minimum working capacitance of at least 50 nF.

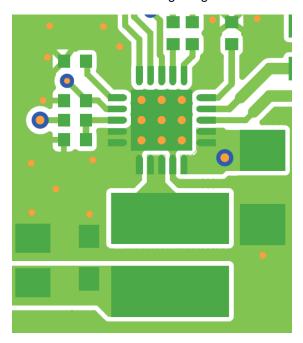
#### **LOW-VOLTAGE OPERATION**

The lowest gain setting is optimized for 50  $V_{PP}$  with a boost voltage of 30 V. Some applications may not need 50  $V_{PP}$ , so the user may elect to program the boost converter as low as 15 V to improve efficiency. When using boost voltages lower than 30 V, some special considerations are in order. First, to reduce boost ripple to an acceptable level, a 50 V rated, 0.22  $\mu$ F boost capacitor is recommended. Second, the full-scale input range may need adjustment to avoid clipping. Normally, a 1.8 V, single-ended PWM signal will give 50  $V_{PP}$  at the lowest gain. For example, if the boost voltage is set to 25 V for a 40  $V_{PP}$  full-scale output signal, the full-scale input range drops to 1.44 V for single-ended PWM inputs. An input voltage divider may be desired in this case if a 1.8V I/O is used as a PWM source.

#### THERMAL/LAYOUT CONSIDERATIONS

To achieve optimum device performance, use of the thermal footprint outlined by this datasheet is recommended. See land pattern diagram for exact dimensions. The DRV8662 power pad must be soldered directly to the thermal pad on the printed circuit board. The printed circuit board thermal pad should be connected to the ground net with thermal vias to any existing backside/internal copper ground planes. Connection to a ground plane on the top layer near the corners of the device is also recommended.

Another key layout consideration is to keep the boost programming resistors (R1 and R2) as close as possible to the FB pin of the DRV8662. Care should be taken to avoid getting the FB trace near the SW trace.





#### **CURRENT CONSUMPTION CALCULATION**

It is useful to understand how the voltage driven onto a piezo actuator relates to the current consumption from the power supply. Modeling a piezo element as a pure capacitor is reasonably accurate. The equation for the current through a capacitor for an applied sinusoid is given by Equation 3

$$I_{Capacitor(Peak)} = 2\pi \times f \times C \times V_{P}$$
(3)

where f is the frequency of the sinusoid in Hz, C is the capacitance of the piezo load in farads, and  $V_P$  is the peak voltage. At the power supply (usually a battery), the actuator current is multiplied by the boost-supply ratio and divided by the efficiency of the boost converter as shown by Equation 4.

$$I_{BAT(Peak)} = 2\pi \times f \times C \times V_P \times \frac{V_{Boost}}{V_{BAT} \times \mu_{Boost}}$$
(4)

Substituting typical values for the variables of this equation yields a typical peak current seen by the battery with a sine input as in Equation 5.

$$I_{BAT(Peak)} = 2\pi \times 300 \text{ Hz} \times 50 \text{ nF} \times 100 \times \frac{105}{3.6 \times 0.7} = 392 \text{ mA}$$
 (5)

#### INPUT FILTER CONSIDERATIONS

Depending on the quality of the source signal provided to the DRV8662, an input filter may be required. Some key factors to consider are whether the source is generated from a DAC or from PWM and the out-of-band content generated. If proper anti-image rejection filtering is used to eliminate image components, the filter can possibly be eliminated depending on the magnitude of the out-of-band components. If PWM is used, at least a 1<sup>st</sup> order RC filter is required. The PWM sample rate should be greater than 30 kHz to keep the PWM ripple from reaching the piezo element and dissipating unnecessary power. A 2<sup>nd</sup> order RC filter may be desirable to further eliminate out-of-band signal content to further drive down power dissipation and eliminate audible noise.

## STARTUP/SHUTDOWN SEQUENCING

A simple startup sequence should be employed to maintain smooth haptic operation. If the sequence is not followed, unintended haptic events or sounds my occur. Use the following steps to play back each haptic waveform.

#### **PWM Source**

- 1. Send 50% duty cycle from the processor to the DRV8662 input filter. This is to allow the source and input filter to settle before the DRV8662 is fully enabled. At the same time (or on the next available processor cycle), transition the DRV8662 enable pin from logic low to logic high.
- 2. Wait 2 ms to ensure that the DRV8662 circuitry is fully enabled and settled.
- 3. Begin and complete playback of the haptic waveform. The haptic waveform PWM should end with a 50% duty cycle to bring the differential output back to 0 V.
- 4. Transition the DRV8662 enable pin from high to low and power down the PWM source.

#### **DAC Source**

- 1. Set the DAC to its mid-scale code. This is to allow the source and input capacitors to settle before the DRV8662 is fully enabled. At the same time (or on the next available processor cycle), transition the DRV8662 enable pin from logic low to logic high.
- 2. Wait 2 ms to ensure that the DRV8662 circuitry is fully enabled and settled.
- 3. Begin and complete playback of the haptic waveform. The haptic waveform should end with a mid-scale DAC code to bring the differential output back to 0 V.
- 4. Transition the DRV8662 enable pin from high to low and power down the DAC source.



#### SYSTEM DIAGRAMS

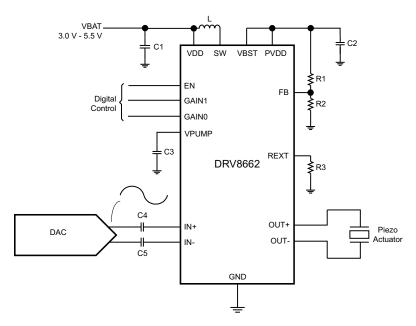


Figure 13. DRV8662 System Diagram with DAC Input

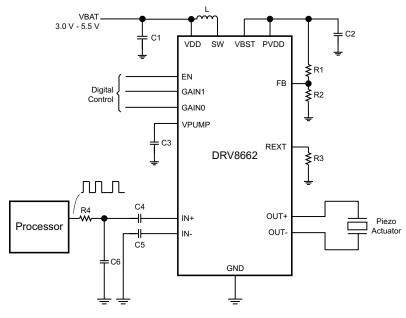


Figure 14. DRV8662 System Diagram with Filtered Single-Ended PWM Input





25-Jun-2012

#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
COMBOAUDIODISPLAY	ACTIVE			0		TBD	Call TI	Call TI	
DRV8662RGPR	ACTIVE	QFN	RGP	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-4-260C-72 HR	
DRV8662RGPT	ACTIVE	QFN	RGP	20	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-4-260C-72 HR	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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PACKAGE MATERIALS INFORMATION

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# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8662RGPR	QFN	RGP	20	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
DRV8662RGPT	QFN	RGP	20	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

**PACKAGE MATERIALS INFORMATION** 

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8662RGPR	QFN	RGP	20	3000	367.0	367.0	35.0
DRV8662RGPT	QFN	RGP	20	250	210.0	185.0	35.0

# RGP (S-PVQFN-N20) PLASTIC QUAD FLATPACK NO-LEAD 4,15 3,85 A В 15 11 10 16 4,15 3,85 20 6 Pin 1 Index Area Top and Bottom 0,20 Nominal Lead Frame 1,00 0,80 Seating Plane \_\_\_\_\_0,08 C Seating Height $\frac{0,05}{0,00}$ C THERMAL PAD 20 SIZE AND SHAPE 4X 2,00 SHOWN ON SEPARATE SHEET 16 10 0,50 15 $20X \frac{0,30}{0,18}$

NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.

0,10 M C A B 0,05 M C

4203555/G 07/11

⚠ Check thermal pad mechanical drawing in the product datasheet for nominal lead length dimensions.



Bottom View

# RGP (S-PVQFN-N20)

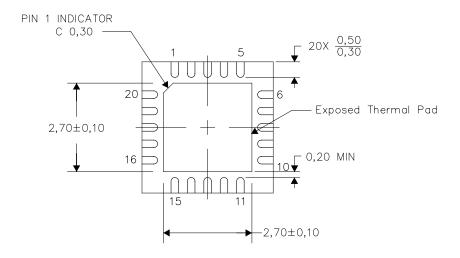
## PLASTIC QUAD FLATPACK NO-LEAD

## THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

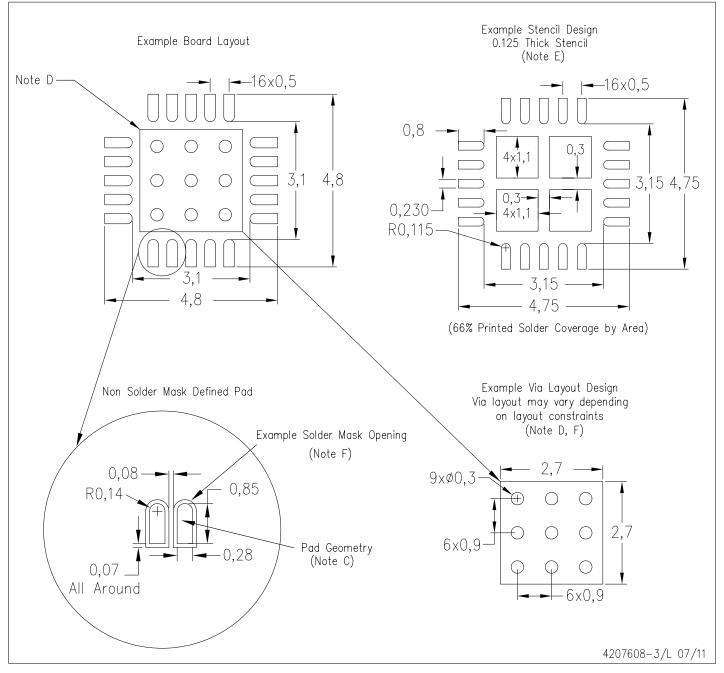
4206346-3/X 02/12

NOTES: A. All linear dimensions are in millimeters



# RGP (S-PVQFN-N20)

# PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="http://www.ti.com">www.ti.com</a>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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